

## NCE N-Channel Super Trench Power MOSFET

### Description

The NCEP02T10 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### General Features

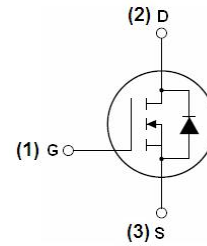
- $V_{DS} = 200V, I_D = 100A$   
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02T10	NCEP02T10	TO-220-3L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	100	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	70.7	A
Pulsed Drain Current	$I_{DM}$	400	A
Maximum Power Dissipation	$P_D$	300	W
Derating factor		2	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 1)</sup>	$E_{AS}$	1216	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.5	$^{\circ}\text{C}/\text{W}$
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## Electrical Characteristics ( $T_c=25^{\circ}\text{C}$ unless otherwise noted)

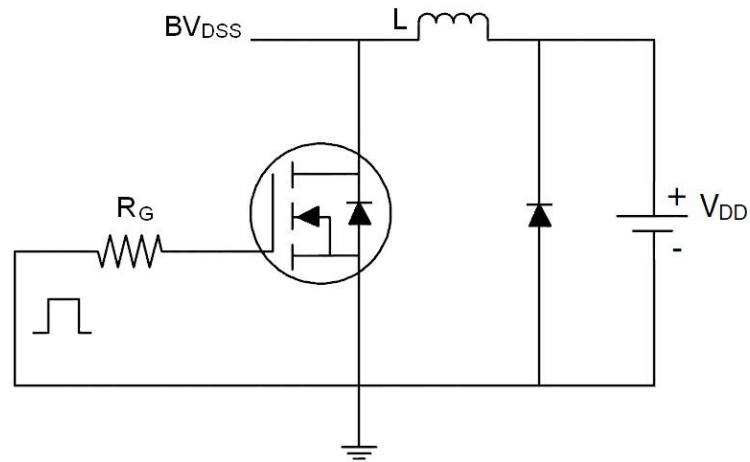
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=200V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=50A$	-	10	12	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V, I_D=50A$	70	-	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=100V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	6000	-	PF
Output Capacitance	$C_{oss}$		-	425	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	16	-	PF
<b>Switching Characteristics</b> <small>(Note 2)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=100V, I_D=50A$ $V_{GS}=10V, R_G=4.7\Omega$	-	18	-	nS
Turn-on Rise Time	$t_r$		-	26	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	41	-	nS
Turn-Off Fall Time	$t_f$		-	11	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=100V, I_D=50A,$ $V_{GS}=10V$	-	87		nC
Gate-Source Charge	$Q_{gs}$		-	32		nC
Gate-Drain Charge	$Q_{gd}$		-	17.5		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=100A$	-		1.2	V
Diode Forward Current	$I_S$		-	-	100	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = 50A$	-	140		nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$	-	600		nC

### Notes:

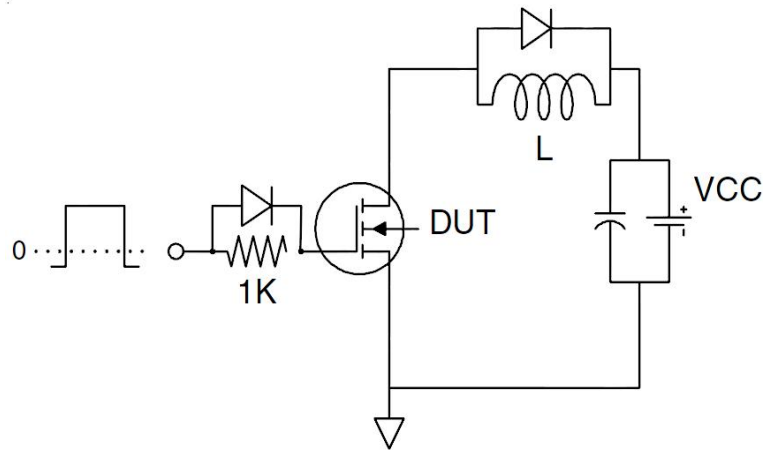
- EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$
- Guaranteed by design, not subject to production
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_J(\text{MAX})=175^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.

**Test Circuit**

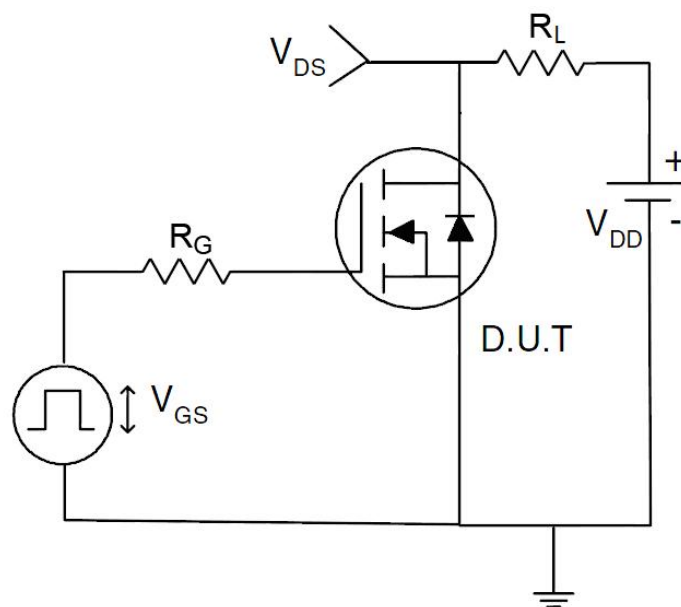
**1)  $E_{AS}$  test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics

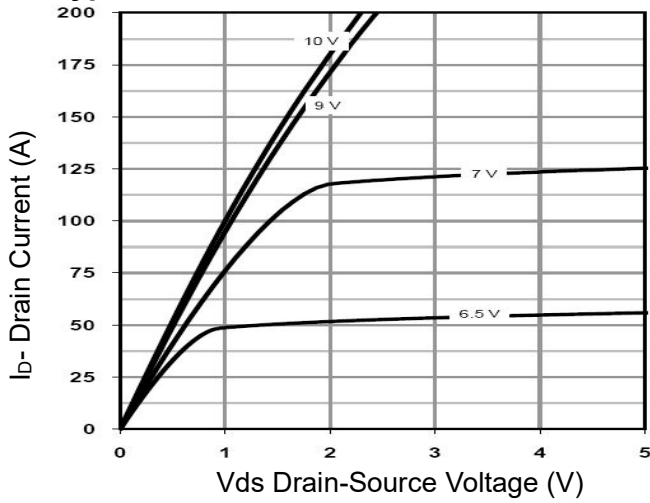


Figure 1 Output Characteristics

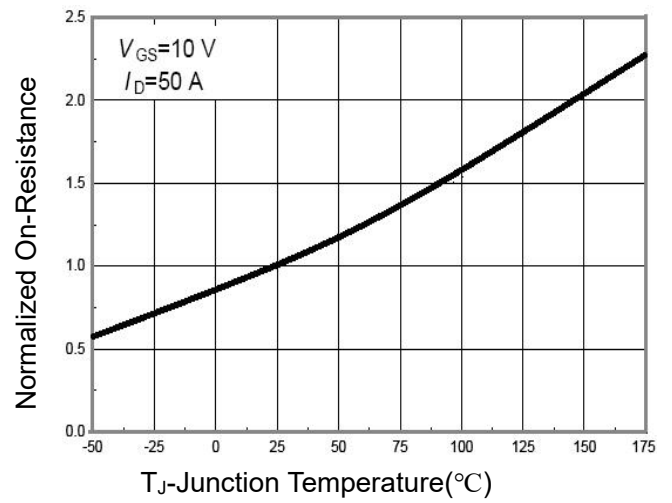


Figure 4 Rdson-Junction Temperature

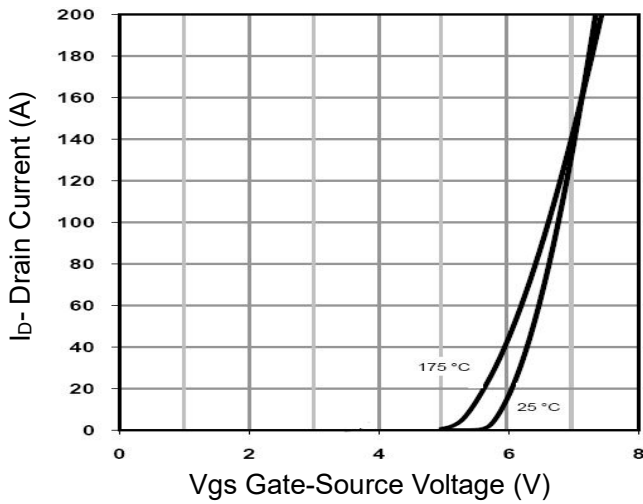


Figure 2 Transfer Characteristics

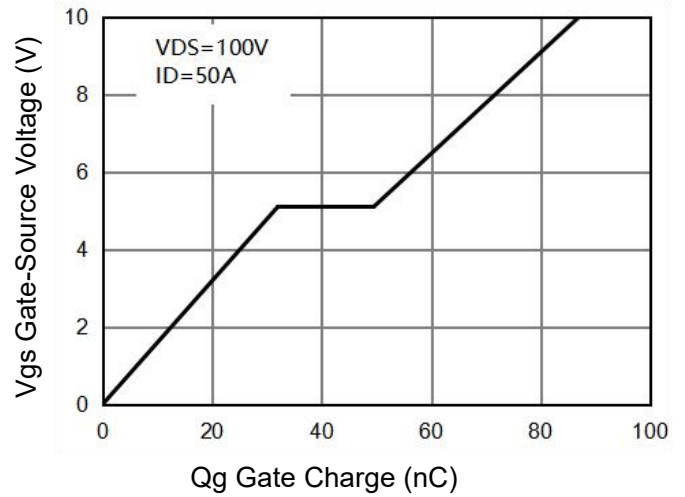


Figure 5 Gate Charge

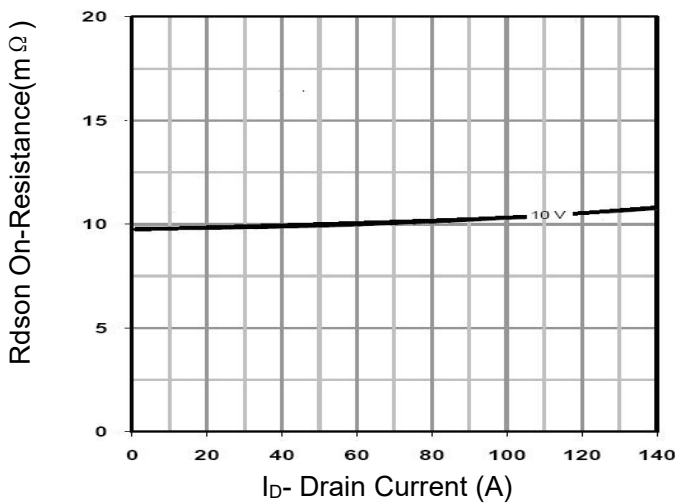


Figure 3 Rdson- Drain Current

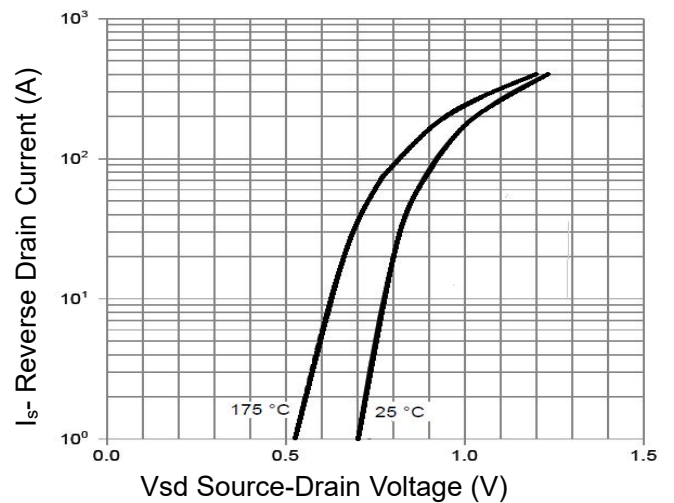
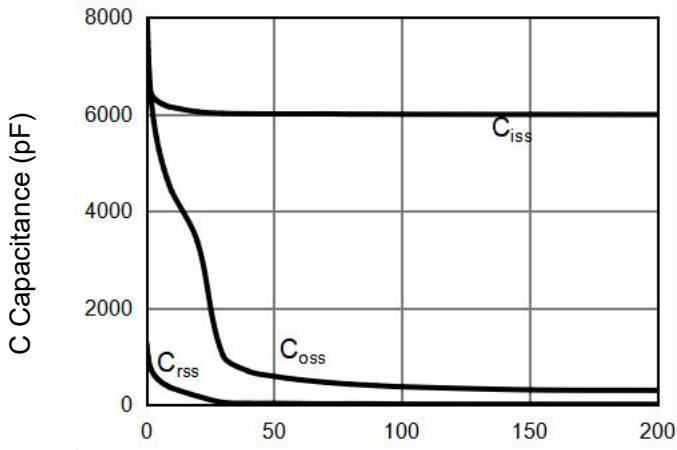
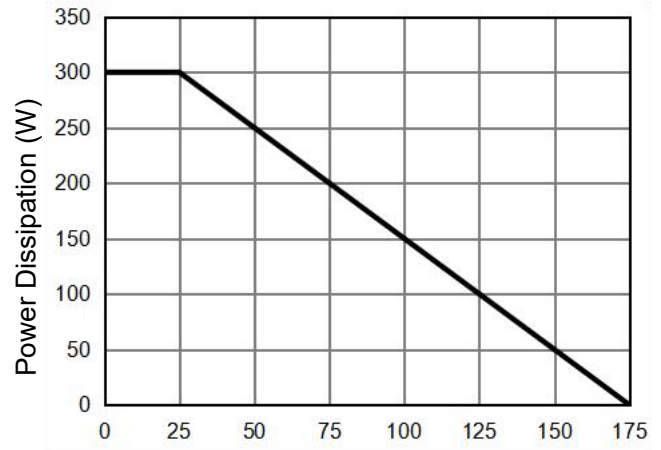


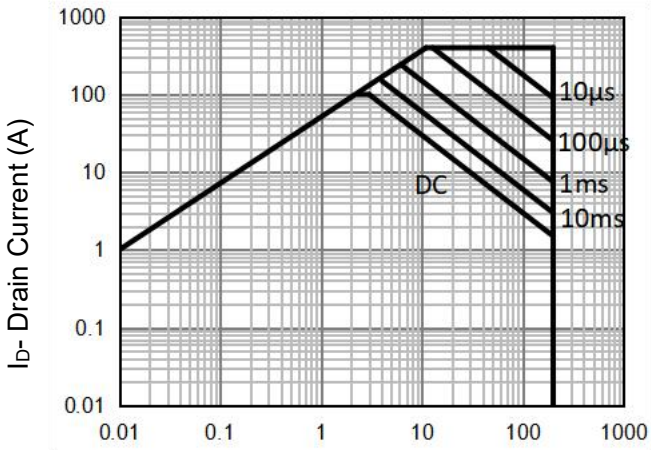
Figure 6 Source- Drain Diode Forward



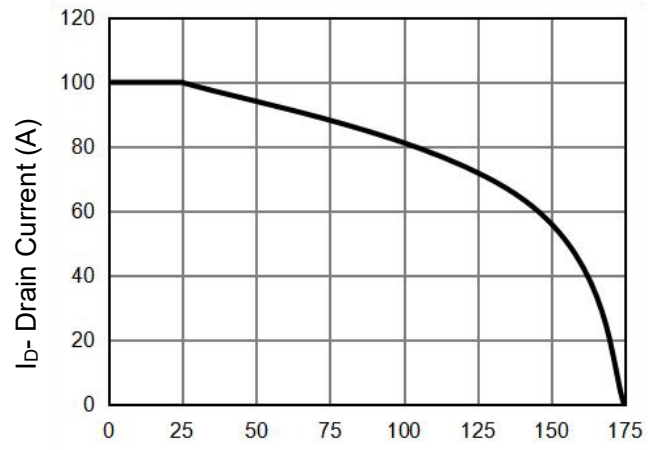
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



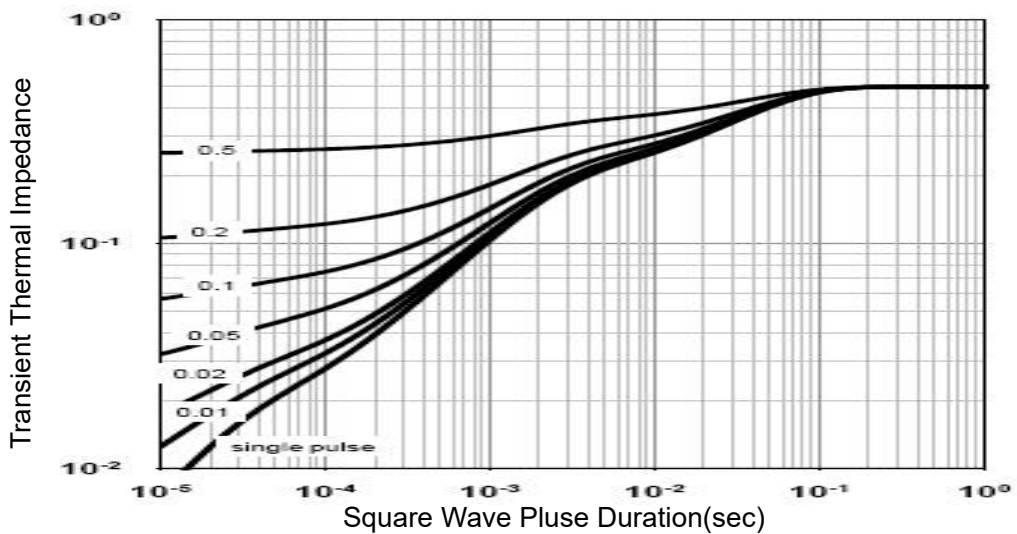
TA-Junction Temperature(°C)  
**Figure 9 Power De-rating**



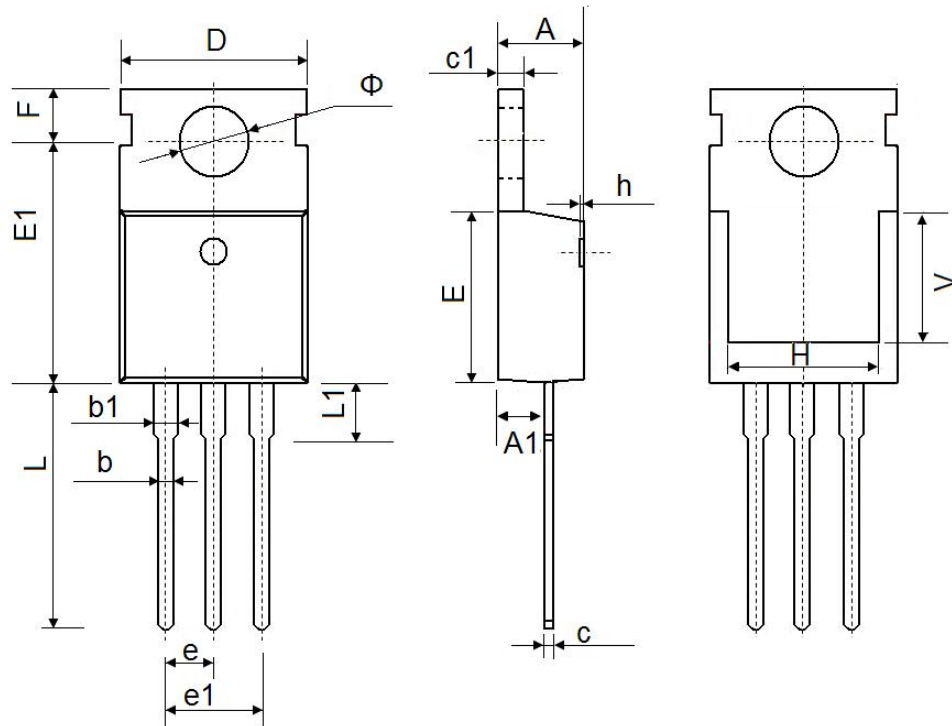
Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area** (Note 3)



TA-Junction Temperature (°C)  
**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-220-3L Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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